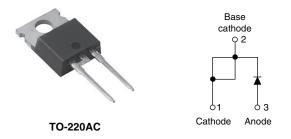
Vishay Semiconductors





Ultrafast Rectifier, 8 A FRED Pt[®]



PRODUCT SUMMARY									
Package	TO-220AC								
I _{F(AV)}	8 A								
V _R	1200 V								
V _F at I _F at 125 °C	1.95 V								
t _{rr}	42 ns								
T _J max.	175 °C								
Diode variation	Single die								

FEATURES

- · Ultrafast and soft recovery time
- Optimized forward voltage drop
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Rugged design
- Good thermal performance
- AEC-Q101 gualified available
- Meets JESD 201 class 2 whisker test
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Ultrafast recovery rectifiers designed with optimized forward voltage drop, ultrafast recovery time and soft recovery.

Polyimide passivated with a planar structure and platinum-doped lifetime control guarantee ruggedness, reliability and offer a solid value for efficiency and thermal performance.

These devices are intended for use in the boost stage in the AC/DC section of SMPS, high frequency output rectification of battery chargers, inverters for solar inverters or as freewheeling diodes in motor drives.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	T _C = 140 °C, D = 0.50	8							
Non repetitive peak surge current	I _{FSM}	$T_C = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ sine wave}$	80	А						
Repetitive peak forward current	I _{FM}		16							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)										
PARAMETER	TYP.	MAX.	UNITS							
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 200 μA	1200	-	-					
Forward voltage	V	$I_F = 8 A$		2.05	2.55	V				
	V _F	I _F = 8 A, T _J = 125 °C	-	1.95	2.37					
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	55	μA				
neverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	100	μΑ				
Junction capacitance	CT	V _R = 200 V		8	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				



RoHS COMPLIANT HALOGEN



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		I _F = 1.0 A, dI _F /dt =	100 A/ μ s, V _R = 30 V	-	42	-			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	144	-	ns A		
		T _J = 125 °C		-	204	-			
Dook roooyon, ourront	I _{RRM}	T _J = 25 °C	I _F = 8 A dI _F /dt = 100 A/μs V _R = 390 V	-	5	-			
Peak recovery current		T _J = 125 °C		-	7.2	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	370	-	20		
		T _J = 125 °C		-	745	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Thermal resistance, junction to case	R _{thJC}		-	1.25	1.5					
Thermal resistance, junction to ambient			-	54	60	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.18	0.4					
Weight			-	0.2	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device	Case style: TO-220AC 8ETU12H									

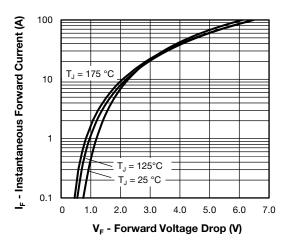


Fig. 1 - Typical Forward Voltage Drop Characteristics

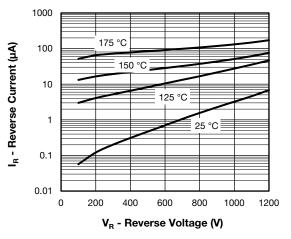


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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VS-8ETU12HN3

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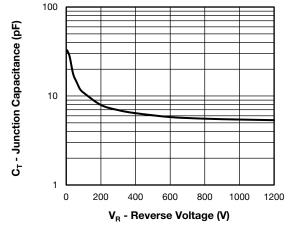


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

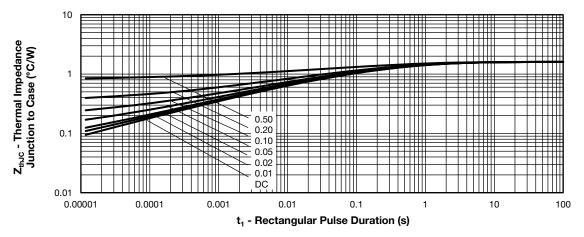


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

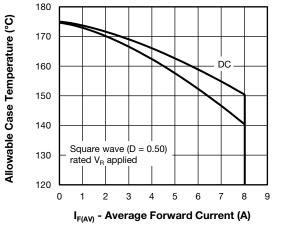


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

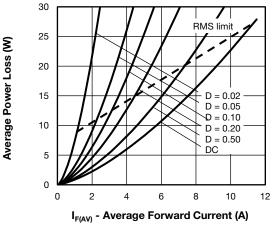


Fig. 6 - Forward Power Loss Characteristics

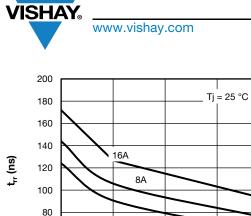
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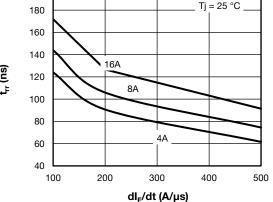


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

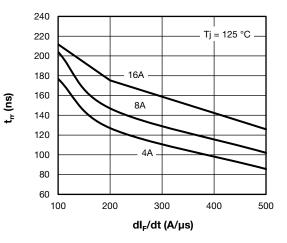


Fig. 8 - Typical Reverse Recovery Time vs. dI_F/dt

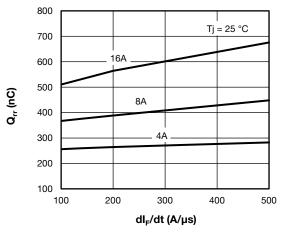


Fig. 9 - Typical Stored Charge vs. dl_F/dt

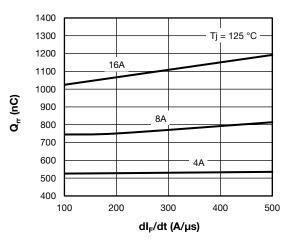


Fig. 10 - Typical Stored Charge vs. dl_F/dt

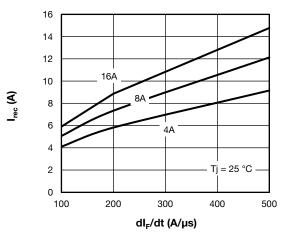


Fig. 11 - Typical Reverse Current vs. dl_F/dt

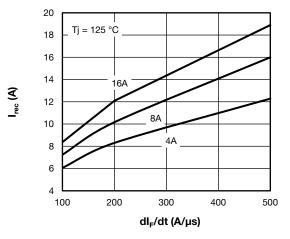


Fig. 12 - Typical Reverse Current vs. dl_F/dt

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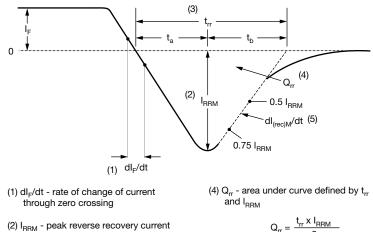
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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_E to point where a line passing through 0.75 $\mathrm{I}_{\mathrm{RRM}}$ and 0.50 $\mathrm{I}_{\mathrm{RRM}}$ extrapolated to zero current.

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 13 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

www.vishay.com

Device code	VS-	8	Е	т	υ	12	н	N3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)
	1 - 2 - 3 - 4 -	Visł Cur Circ	nay Serr rent rati	niconduc ng (8 = 8 iguratior	ctors pro 8 A)	oduct	ode	0
	5 - 6 - 7 - 8 -	U = Volt H = Env	age rati AEC-Q rironmer	t recove ng (12 = 101 qua ntal digit en-free,	= 1200 V Ilified :	,	nt. and 1	totally le

ORDERING INFORMATION (Example) **QUANTITY PER T/R PREFERRED P/N** MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION VS-8ETU12HN3 50 1000 Antistatic plastic tube

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95221					
Part marking information	www.vishay.com/doc?95068					

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TO-220AC

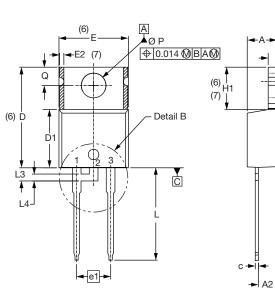
B Seating

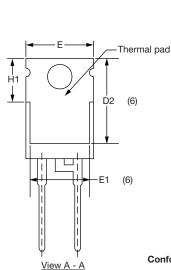
A-

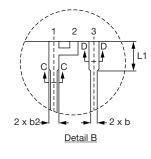
-A1

plane

DIMENSIONS in millimeters and inches









Conforms to JEDEC[®] outline TO-220AC

⊕ 0.015 BA

SYMBOL -	MILLIM	MILLIMETERS		INCHES		NOTES SY	SYMBOL	MILLIMETERS		INCHES		NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040			H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4		L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068			L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4		L3	1.78	2.13	0.070	0.084	
с	0.36	0.61	0.014	0.024			L4	0.76	1.27	0.030	0.050	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.73	0.139	0.147	
D	14.85	15.25	0.585	0.600	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								
D2	11.68	12.88	0.460	0.507	6							
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- (4) Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed

⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

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